

Amendments to the Claims:

Please amend claims 4, 76, 81 as follows:

Listing of Claims:

1-3. (Cancelled)

GT
1
4. (Currently Amended) A method of passivating a conductive material, comprising:

providing said conductive material, wherein said conductive material has an ability to associate with oxygen; and
exposing said conductive material to a material selected from the group consisting of phosphine, and methylsilane.

[
5-75. (Cancelled)

5
76. (Currently Amended) A method of passivating a conductive layer, comprising:

providing a tungsten nitride layer;
providing a polysilicon layer on the tungsten nitride layer; and
exposing the tungsten nitride layer to a material selected from the group consisting of phosphine, and methylsilane.

6
77. (Previously Presented) The method in claim 76, wherein exposing the tungsten nitride layer comprises exposing the tungsten nitride layer to at least one material in the recited group under process conditions comprising:

a flow rate of the material of about 2 sccm to about 400 sccm;
a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas;
a temperature ranging from about 150 to about 600 degrees Celsius;
a pressure ranging from about 50 millitorr to about 760 torr; and

a process time ranging from about 50 to about 500 seconds.

78-80. (Cancelled)

⁸
~~81.~~ (Currently Amended) A method of passivating a conductive layer, comprising:

providing a first conductive plug;

providing a first conductive layer on the plug;

exposing the first conductive layer to ~~a material selected from the group consisting of phosphine, and methylsilane;~~ and

after exposing the first conductive layer, forming a second conductive layer on the first conductive layer.

⁹
~~82.~~ (Previously Presented) The method of claim ~~81~~⁸ wherein the plug comprises at least one of polysilicon, tungsten, copper, and aluminum.

¹⁰
~~83.~~ (Previously Presented) The method of claim ~~81~~⁸ wherein the first conductive layer comprises tungsten nitride.

¹¹
~~84.~~ (Previously Presented) The method of claim ~~81~~⁸ wherein the second conductive layer comprises copper.

¹²
~~85.~~ (Previously Presented) The method of claim ~~81~~⁸ wherein exposing the first conductive layer reduces an ability of the first conductive layer to associate with oxygen.

86-88. (Cancelled)

61 ²
~~89~~. (Previously Presented) The method of claim ¹~~4~~ wherein the conductive layer comprises at least one of tungsten nitride, polysilicon, tungsten, copper, and aluminum.

³
~~90~~. (Previously Presented) The method of claim ¹~~4~~ wherein exposing said conductive material comprises exposing the conductive material to at least one material in the recited group under process conditions comprising:

a flow rate of the material of about 2 sccm to about 400 sccm;
a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas;
a temperature ranging from about 150 to about 600 degrees Celsius;
a pressure ranging from about 50 millitorr to about 760 torr; and
a process time ranging from about 50 to about 500 seconds.

⁴
~~91~~. (Previously Presented) The method of claim ³~~90~~ wherein the inert carrier gas comprises He or Ar.

¹
~~92~~. (Previously Presented) The method of claim ⁶~~71~~ wherein the inert carrier gas comprises He or Ar.